

# MJD128T4G (PNP)

## Complementary Darlington Power Transistor

### DPAK For Surface Mount Applications

Designed for general purpose amplifier and low speed switching applications.

#### Features

- Monolithic Construction With Built-in Base-Emitter Shunt Resistors
- High DC Current Gain:  $h_{FE} = 2500$  (Typ) @  $I_C = 4.0$  Adc
- Epoxy Meets UL 94 V-0 @ 0.125 in.
- ESD Ratings:
  - ♦ Human Body Model,  $3B > 8000$  V
  - ♦ Machine Model,  $C > 400$  V
- NJV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These are Pb-Free Devices\*

#### MAXIMUM RATINGS

| Rating                                                                                    | Symbol         | Value          | Unit                     |
|-------------------------------------------------------------------------------------------|----------------|----------------|--------------------------|
| Collector-Emitter Voltage                                                                 | $V_{CEO}$      | 120            | Vdc                      |
| Collector-Base Voltage                                                                    | $V_{CB}$       | 120            | Vdc                      |
| Emitter-Base Voltage                                                                      | $V_{EB}$       | 5              | Vdc                      |
| Collector Current<br>Continuous<br>Peak                                                   | $I_C$          | 8<br>16        | Adc                      |
| Base Current                                                                              | $I_B$          | 120            | mAdc                     |
| Total Power Dissipation<br>@ $T_C = 25^\circ\text{C}$<br>Derate above $25^\circ\text{C}$  | $P_D$          | 20<br>0.16     | W<br>W/ $^\circ\text{C}$ |
| Total Power Dissipation*<br>@ $T_A = 25^\circ\text{C}$<br>Derate above $25^\circ\text{C}$ | $P_D$          | 1.75<br>0.014  | W<br>W/ $^\circ\text{C}$ |
| Operating and Storage Junction<br>Temperature Range                                       | $T_J, T_{stg}$ | -65 to<br>+150 | $^\circ\text{C}$         |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

#### THERMAL CHARACTERISTICS

| Characteristic                                   | Symbol          | Max  | Unit               |
|--------------------------------------------------|-----------------|------|--------------------|
| Thermal Resistance, Junction-to-Case             | $R_{\theta JC}$ | 6.25 | $^\circ\text{C/W}$ |
| Thermal Resistance, Junction-to-Ambient (Note 1) | $R_{\theta JA}$ | 71.4 | $^\circ\text{C/W}$ |

1. These ratings are applicable when surface mounted on the minimum pad sizes recommended.

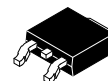
\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



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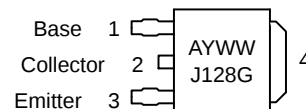
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**SILICON  
POWER TRANSISTOR  
8 AMPERES  
120 VOLTS, 20 WATTS**



**DPAK  
CASE 369C  
STYLE 1**

#### MARKING DIAGRAM



A = Assembly Location  
Y = Year  
WW = Work Week  
J128 = Device Code  
G = Pb-Free Package

#### ORDERING INFORMATION

| Device       | Package           | Shipping†         |
|--------------|-------------------|-------------------|
| MJD128T4G    | DPAK<br>(Pb-Free) | 2,500/Tape & Reel |
| NJVMJD128T4G | DPAK<br>(Pb-Free) | 2,500/Tape & Reel |

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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## ELECTRICAL CHARACTERISTICS ( $T_C = 25^\circ\text{C}$ unless otherwise noted)

| Characteristic | Symbol | Min | Max | Unit |
|----------------|--------|-----|-----|------|
|----------------|--------|-----|-----|------|

### OFF CHARACTERISTICS

|                                                                              |               |     |    |               |
|------------------------------------------------------------------------------|---------------|-----|----|---------------|
| Collector-Emitter Sustaining Voltage<br>( $I_C = 30\text{ mA}$ , $I_B = 0$ ) | $V_{CE(sus)}$ | 120 | –  | Vdc           |
| Collector Cutoff Current<br>( $V_{CE} = 120\text{ Vdc}$ , $I_B = 0$ )        | $I_{CEO}$     | –   | 5  | mA            |
| Collector Cutoff Current<br>( $V_{CB} = 100\text{ Vdc}$ , $I_E = 0$ )        | $I_{CBO}$     | –   | 10 | $\mu\text{A}$ |
| Emitter Cutoff Current<br>( $V_{BE} = 5\text{ Vdc}$ , $I_C = 0$ )            | $I_{EBO}$     | –   | 2  | mA            |

### ON CHARACTERISTICS

|                                                                                                                                        |               |             |             |     |
|----------------------------------------------------------------------------------------------------------------------------------------|---------------|-------------|-------------|-----|
| DC Current Gain<br>( $I_C = 4\text{ A}$ , $V_{CE} = 4\text{ Vdc}$ )<br>( $I_C = 8\text{ A}$ , $V_{CE} = 4\text{ Vdc}$ )                | $h_{FE}$      | 1000<br>100 | 12,000<br>– | –   |
| Collector-Emitter Saturation Voltage<br>( $I_C = 4\text{ A}$ , $I_B = 16\text{ mA}$ )<br>( $I_C = 8\text{ A}$ , $I_B = 80\text{ mA}$ ) | $V_{CE(sat)}$ | –<br>–      | 2<br>4      | Vdc |
| Base-Emitter Saturation Voltage (1)<br>( $I_C = 8\text{ A}$ , $I_B = 80\text{ mA}$ )                                                   | $V_{BE(sat)}$ | –           | 4.5         | Vdc |
| Base-Emitter On Voltage<br>( $I_C = 4\text{ A}$ , $V_{CE} = 4\text{ Vdc}$ )                                                            | $V_{BE(on)}$  | –           | 2.8         | Vdc |

### DYNAMIC CHARACTERISTICS

|                                                                                                         |            |     |     |     |
|---------------------------------------------------------------------------------------------------------|------------|-----|-----|-----|
| Current-Gain-Bandwidth Product<br>( $I_C = 3\text{ A}$ , $V_{CE} = 4\text{ Vdc}$ , $f = 1\text{ MHz}$ ) | $ h_{fe} $ | 4   | –   | MHz |
| Output Capacitance<br>( $V_{CB} = 10\text{ Vdc}$ , $I_E = 0$ , $f = 0.1\text{ MHz}$ )                   | $C_{ob}$   | –   | 300 | pF  |
| Small-Signal Current Gain<br>( $I_C = 3\text{ A}$ , $V_{CE} = 4\text{ Vdc}$ , $f = 1\text{ kHz}$ )      | $h_{fe}$   | 300 | –   | –   |

2. Pulse Test: Pulse Width  $\leq 300\text{ }\mu\text{s}$ , Duty Cycle  $\leq 2\%$ .

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

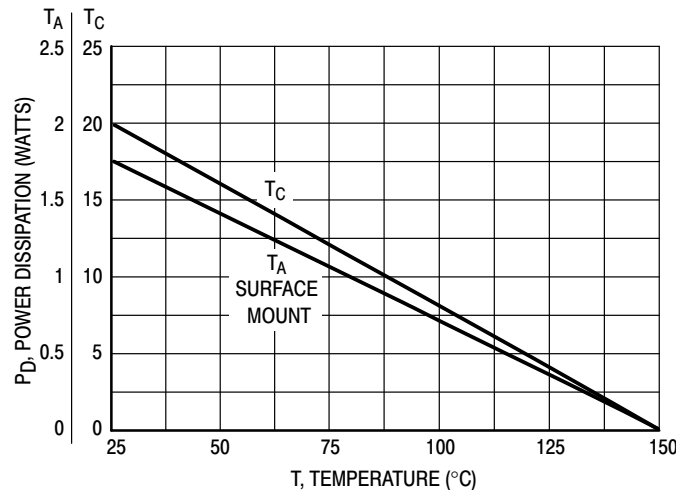


Figure 1. Power Derating

# MJD128T4G (PNP)

## TYPICAL ELECTRICAL CHARACTERISTICS

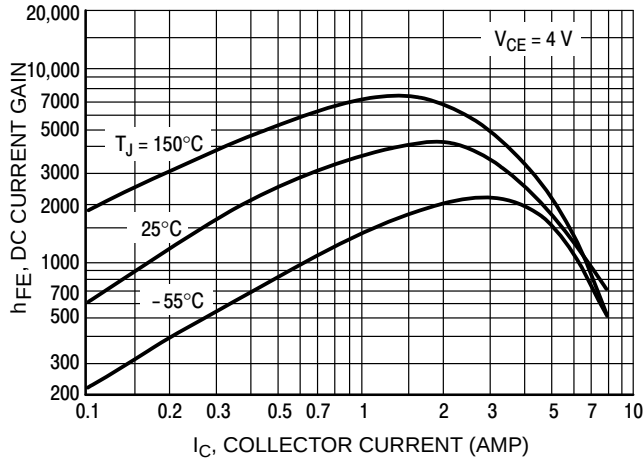


Figure 2. DC Current Gain

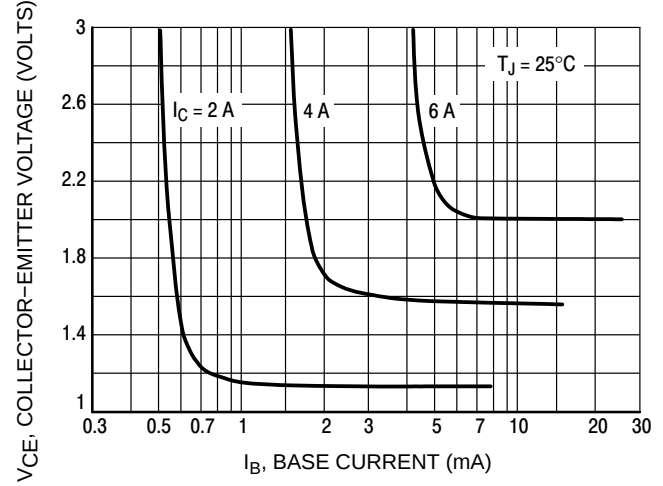


Figure 3. Collector Saturation Region

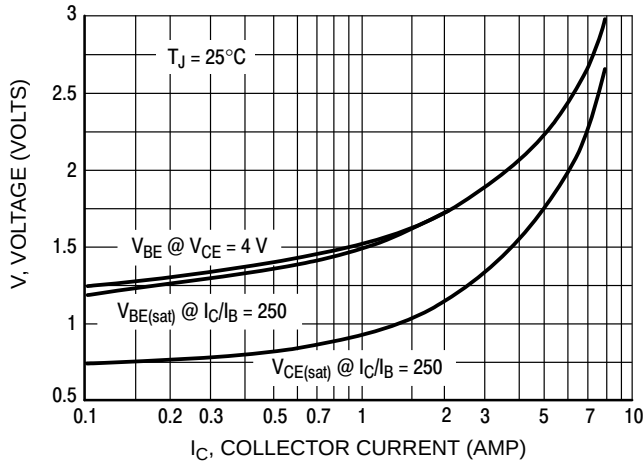


Figure 4. "On" Voltages

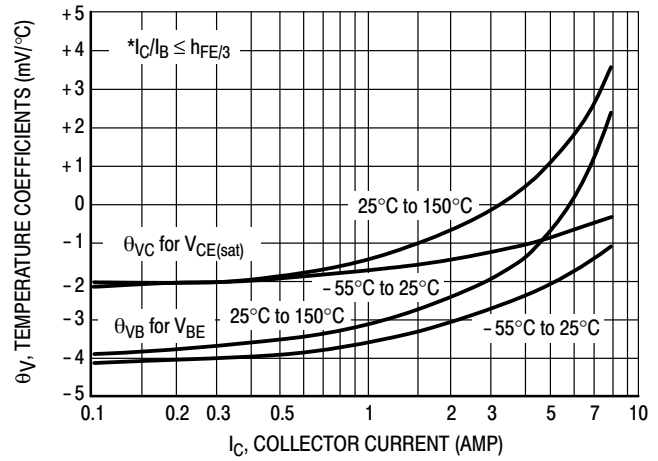


Figure 5. Temperature Coefficients

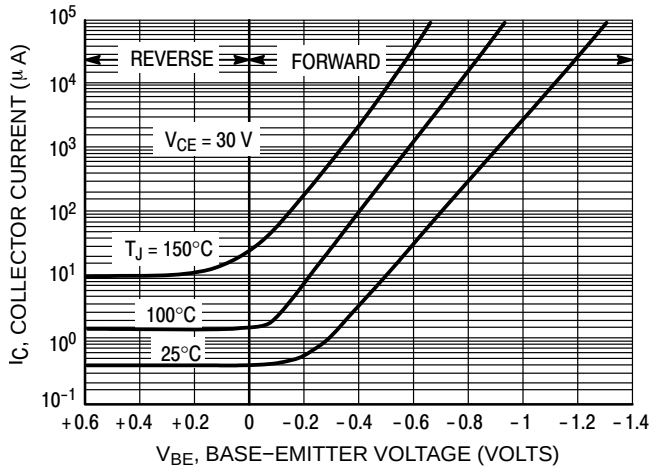


Figure 6. Collector Cut-Off Region

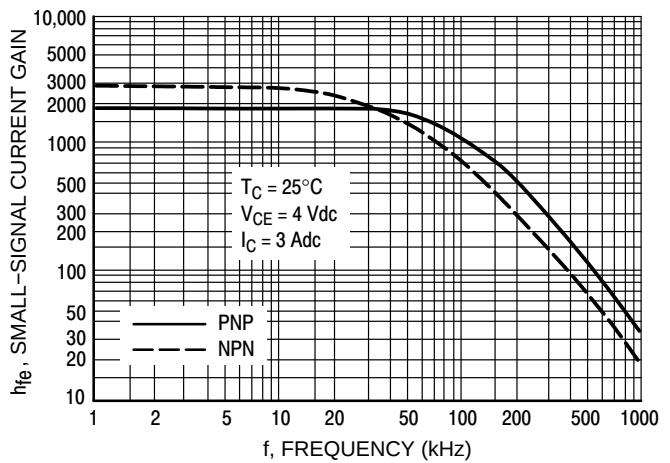


Figure 7. Small-Signal Current Gain

## MJD128T4G (PNP)

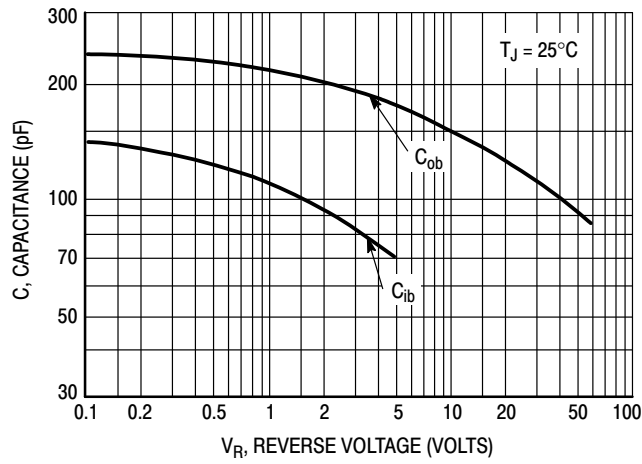


Figure 8. Capacitance

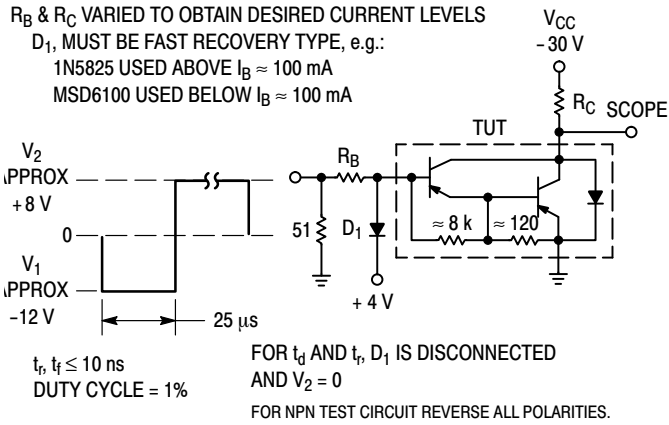


Figure 9. Switching Times Test Circuit

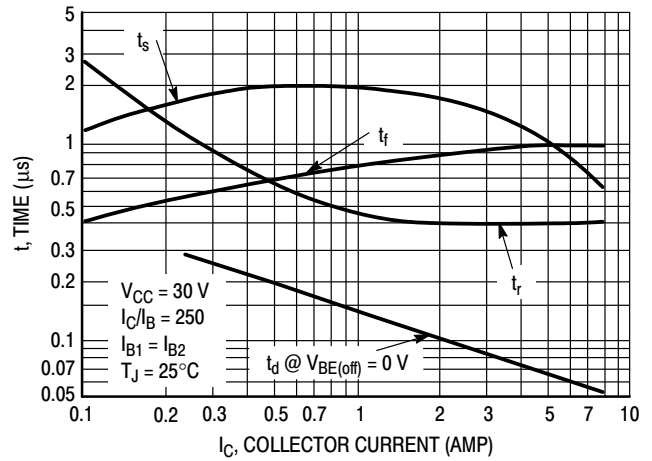


Figure 10. Switching Times

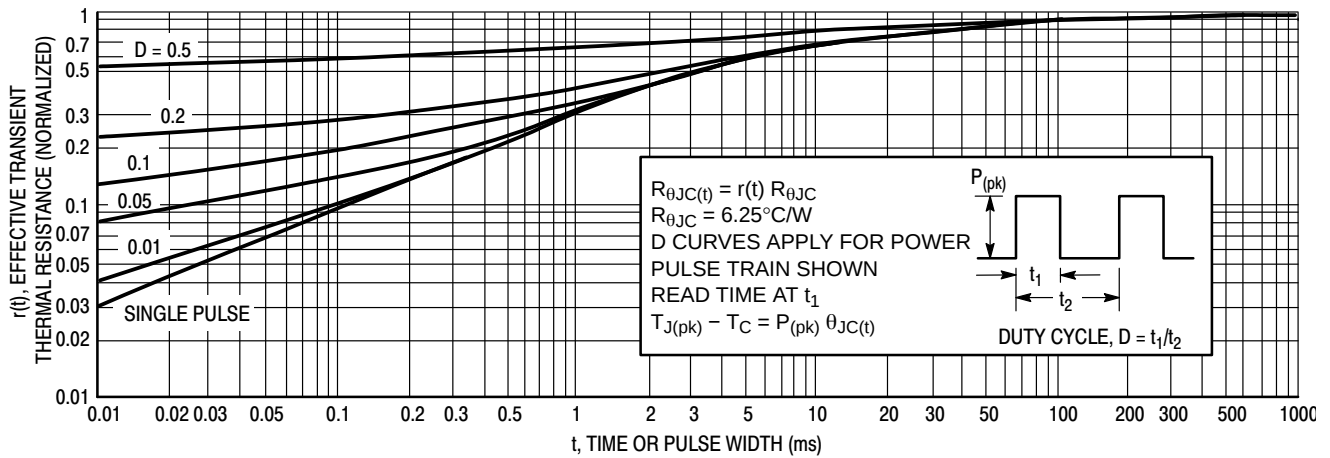
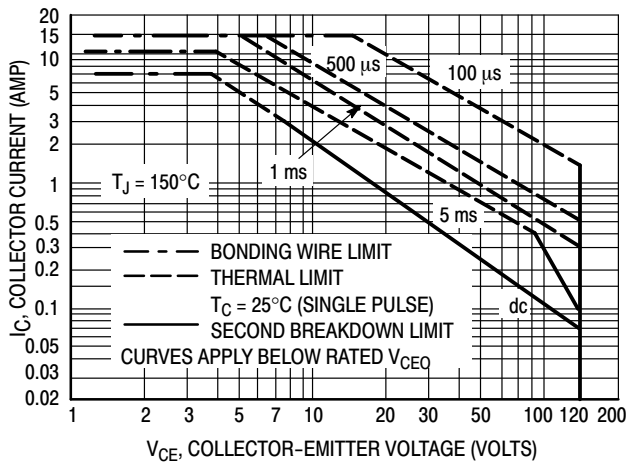


Figure 11. Thermal Response

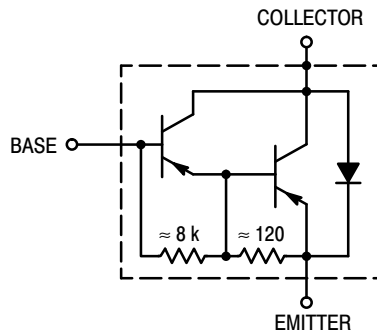
## MJD128T4G (PNP)



**Figure 12. Maximum Forward Bias  
Safe Operating REA**

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate  $I_C - V_{CE}$  limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 12 is based on  $T_{J(pk)} = 150^\circ\text{C}$ ;  $T_C$  is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided  $T_{J(pk)} < 150^\circ\text{C}$ .  $T_{J(pk)}$  may be calculated from the data in Figure 11. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.



**Figure 13. Darlington Schematic**

# MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS

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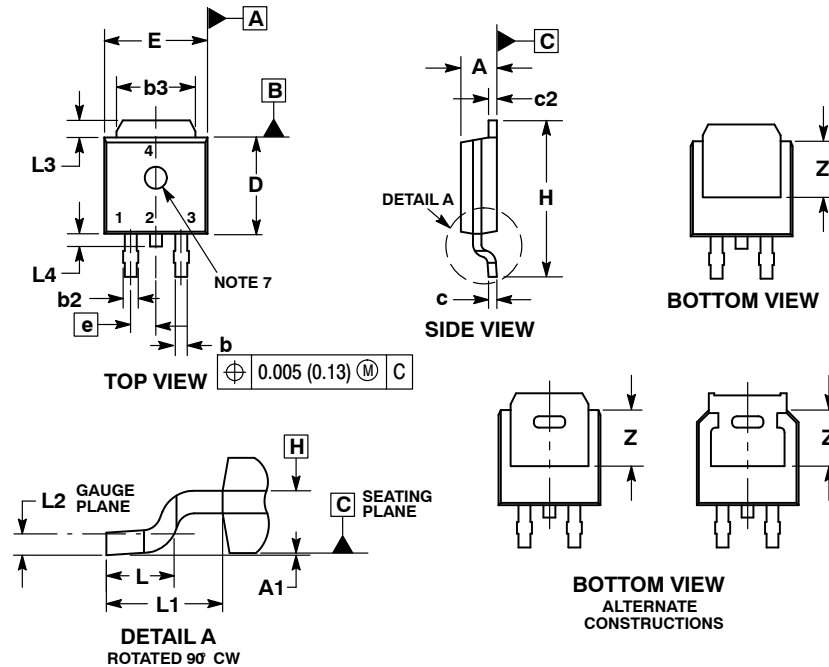
ON



SCALE 1:1

## DPAK (SINGLE GAUGE) CASE 369C ISSUE F

DATE 21 JUL 2015



### NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCHES.
3. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS b3, L3 and Z.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.
5. DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
6. DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.
7. OPTIONAL MOLD FEATURE.

| DIM | MIN   | MAX   | MIN  | MAX   |
|-----|-------|-------|------|-------|
| A   | 0.086 | 0.094 | 2.18 | 2.38  |
| A1  | 0.000 | 0.005 | 0.00 | 0.13  |
| b   | 0.025 | 0.035 | 0.63 | 0.89  |
| b2  | 0.028 | 0.045 | 0.72 | 1.14  |
| b3  | 0.180 | 0.215 | 4.57 | 5.46  |
| c   | 0.018 | 0.024 | 0.46 | 0.61  |
| c2  | 0.018 | 0.024 | 0.46 | 0.61  |
| D   | 0.235 | 0.245 | 5.97 | 6.22  |
| E   | 0.250 | 0.265 | 6.35 | 6.73  |
| e   | 0.090 | BSC   | 2.29 | BSC   |
| H   | 0.370 | 0.410 | 9.40 | 10.41 |
| L   | 0.055 | 0.070 | 1.40 | 1.78  |
| L1  | 0.114 | REF   | 2.90 | REF   |
| L2  | 0.020 | BSC   | 0.51 | BSC   |
| L3  | 0.035 | 0.050 | 0.89 | 1.27  |
| L4  | ---   | 0.040 | ---  | 1.01  |
| Z   | 0.155 | ---   | 3.93 | ---   |

### GENERIC MARKING DIAGRAM\*

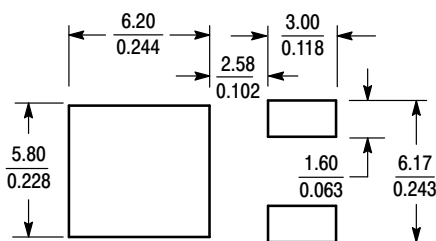


XXXXXX = Device Code  
A = Assembly Location  
L = Wafer Lot  
Y = Year  
WW = Work Week  
G = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking.

- STYLE 1:**  
PIN 1. BASE  
2. COLLECTOR  
3. EMITTER  
4. COLLECTOR
- STYLE 2:**  
PIN 1. GATE  
2. DRAIN  
3. SOURCE  
4. DRAIN
- STYLE 3:**  
PIN 1. ANODE  
2. CATHODE  
3. ANODE  
4. CATHODE
- STYLE 4:**  
PIN 1. CATHODE  
2. ANODE  
3. GATE  
4. ANODE
- STYLE 5:**  
PIN 1. GATE  
2. ANODE  
3. CATHODE  
4. ANODE
- STYLE 6:**  
PIN 1. MT1  
2. MT2  
3. GATE  
4. MT2
- STYLE 7:**  
PIN 1. GATE  
2. COLLECTOR  
3. EMITTER  
4. COLLECTOR
- STYLE 8:**  
PIN 1. N/C  
2. CATHODE  
3. ANODE  
4. CATHODE
- STYLE 9:**  
PIN 1. ANODE  
2. CATHODE  
3. RESISTOR ADJUST  
4. CATHODE
- STYLE 10:**  
PIN 1. CATHODE  
2. ANODE  
3. CATHODE  
4. ANODE

### SOLDERING FOOTPRINT\*



SCALE 3:1 (mm inches)

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERM/D.

|                         |                            |                                                                                                                                                                                     |
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